Product data sheet

1. General description

Dual ultrafast power diodes in a TO247 plastic package.

2. Features and benefits

- · Very low on-state loss
- · Reduces switching losses in associated MOSFET or IGBT
- Low leakage current
- Isolated plastic package

3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
V_R	repetitive peak reverse voltage	DC	600			V
$I_{O(AV)}$	average forward current	δ = 0.5; T _{mb} ≤ 105 °C; square-wave pulse; both diodes conducting	60			А
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μ s; $T_{mb} \le$ 105 °C; square-wave pulse	6	0		А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	240		А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode				А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	2	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.25	-	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 30 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	53	90	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	64	-	ns
		$I_F = 30 \text{ A; } V_R = 200 \text{ V; } dI_F/dt = 200 \text{ A/}\mu\text{s;}$ $T_j = 125 \text{ °C; } Fig. 7$	-	113	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode		A1 A2
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		Sylli123

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV430W-600P	TO247	BYV430W-600PQ	Tube	30	SOT429	25-Mar-2013

7. Marking

Table 4. Marking codes

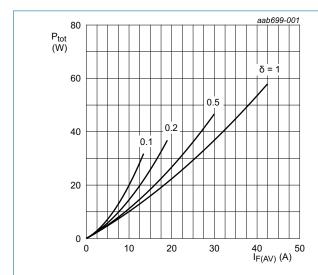
Type number	Marking codes
BYV430W-600P	BYV430W 600P

8. Limiting values

Table 5. Limiting values

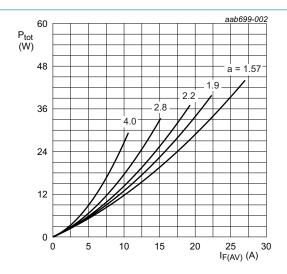
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{O(AV)}$	average forward current	δ = 0.5; T _{mb} ≤ 105 °C; square-wave pulse; both diodes conducting	60	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μs; T_{mb} ≤ 105 °C; square-wave pulse	60	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	240	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode;	264	А
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 0.899 \text{ V; } R_{\text{s}} = 0.0110 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.899 V; R_s = 0.0110 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

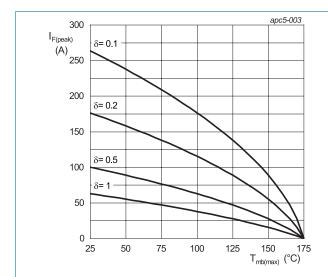


Fig. 3. Current derating as a function of mounting base temperature; per diode

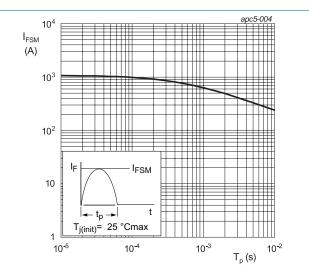


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	1.17	1.5	K/W
	mounting base	with heatsink compound; both diodes conducting	-	0.61	0.75	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W

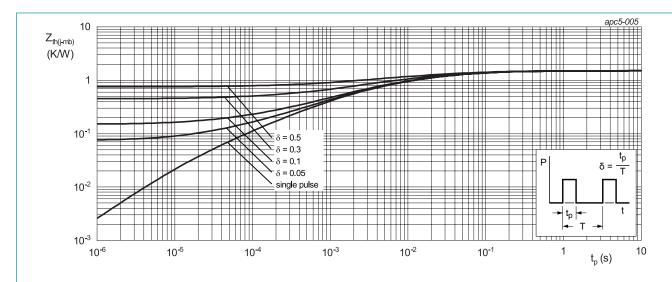
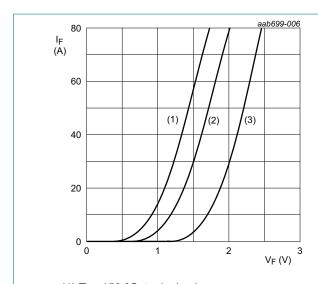


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	l N	/lin	Тур	Max	Unit
Static cha	aracteristics						
V_{F}	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-		1.5	2	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-		1.25	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-		-	10	μA
		V _R = 600 V; T _j = 150 °C	-		-	500	μA
Dynamic	characteristics						'
t _{rr}	reverse recovery time	$I_F = 30 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-		53	90	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-		64	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-		113	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 7	-		7.3	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-		13.5	-	А
Q _r	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-		245	-	nC
		$I_F = 30 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_i = 125 \text{ °C}$; Fig. 7	-		760	-	nC



(1) T_j = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

 $V_o = 0.899 \text{ V}; R_s = 0.0110 \Omega$

Fig. 6. Forward current as a function of forward voltage, per diode

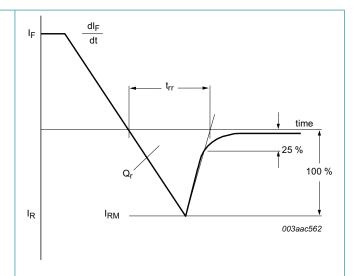
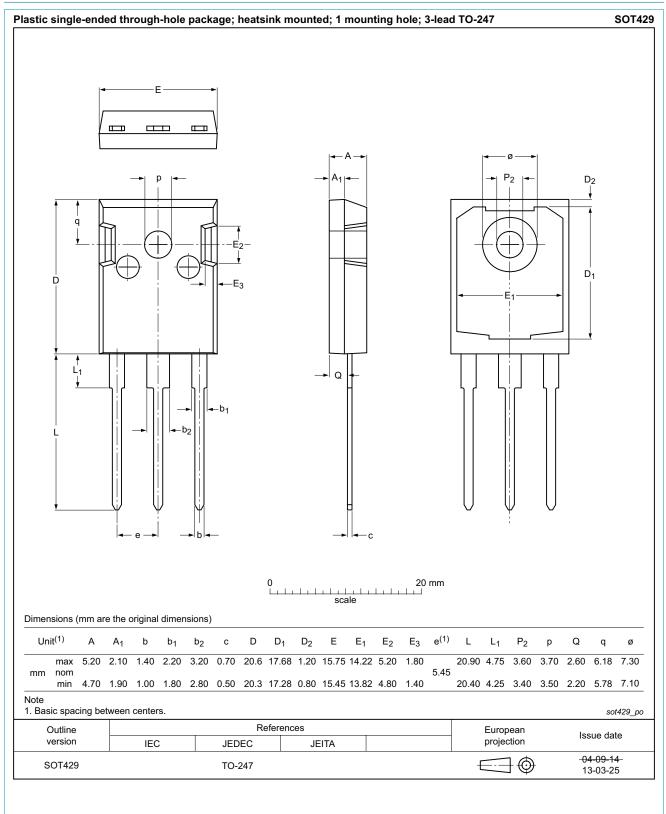


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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